AMENDMENTS

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) An electroplating apparatus ~~for increasing a plated metal thickness uniformity~~ comprising:

a reservoir for holding an electrolyte fluid comprising metal ions for electroplating;

an anode and a cathode, said cathode for holding a wafer provided in said reservoir;

an electrical pathway provided between said cathode and said anode; and

a shield provided between said cathode and said anode, wherein said shield ~~is vertically adjustably movable during an electroplating process~~ is imparted a positive charge to act as an anode.

2. (Currently amended) The electroplating apparatus of claim 1 wherein said shield comprises a ~~body shape selected from the group consisting of a~~ ring-shaped shield body ~~and a plate shaped ring body~~.

3. (Previously presented) The electroplating apparatus of claim 1 further comprising an electrically-conductive material provided on an outer surface of said shield for providing a source of said metal ions.

4. (Original) The electroplating apparatus of claim 3 wherein said electrically-conductive material comprises copper.

5. (Currently amended) The electroplating apparatus of claim 3 further comprising a shield current source electrically connected to said shield ~~for selectively applying at least one of a positive and a negative charge to said shield~~.

6. (Canceled).

7. (Currently amended) An electroplating apparatus for increasing a plated metal thickness uniformity comprising:

a reservoir for holding an electrolyte fluid comprising metal ions for electroplating;

an anode and a cathode, said cathode for holding a wafer provided in said reservoir;

an electrical pathway provided between said cathode and said anode; and

a shield provided between said cathode and said anode, said shield having a ~~body shape selected from the group consisting of a~~ ring-shaped shield body ~~and a plate shaped ring body;~~

~~wherein said shield is vertically adjustably movable during an electroplating process~~ , wherein an electrically-conductive material is provided on said shield and said shield is imparted a positive charge to act as an anode.

8. (Canceled).

9. (Currently amended) The electroplating apparatus of claim 7~~8~~ wherein said electrically-conductive material comprises copper.

10. (Currently amended) The electroplating apparatus of claim 7~~8~~ further comprising a shield current source electrically connected to said shield ~~for selectively applying at least one of a positive and a negative charge to said shield~~.

11. (Canceled).

12. (Currently amended) A method of electroplating a metal on a wafer to increase a plated metal thickness uniformity, comprising:

providing a reservoir containing an electrolyte fluid metal ions for electroplating;

providing an anode and a cathode in said reservoir, said cathode holding a wafer provided in said reservoir;

providing an electrical pathway between said cathode and said anode;

providing a shield in said electrolyte fluid between said cathode and said anode~~, wherein said shield is vertically adjustably movable during an electroplating process~~; ~~and~~

imparting a positive charge to the shield to act as an anode; and

applying a current to said cathode and said anode to plate said metal ions onto said wafer in said electroplating process .

13. (Currently amended) The method of claim 12 wherein said shield comprises a ~~body shape selected from the group consisting of a~~ ring-shaped shield body ~~and a plate shaped ring body~~.

14. (Previously presented) The method of claim 12 further comprising an electrically-conductive material provided on an outer surface of said shield for providing a source of said metal ions.

15. (Original) The method of claim 14 wherein said electrically-conductive material comprises copper.

16. (Currently amended) The method of claim 14 further comprising a shield current source electrically connected to said shield ~~for selectively applying at least one of a positive and a negative charge to said shield~~.

17. (Canceled).

18. (Canceled).

19. (Previously presented) The method of claim 12 wherein said shield has a diameter greater than said anode diameter and is positionally aligned about centered on said wafer.

20-24. (Canceled).

25. (Previously presented) The electroplating apparatus of claim 1, wherein the shield has a diameter greater than the anode and is positionally aligned about centered on the wafer.

26. (Canceled).

27. (Previously presented) The electroplating apparatus of claim 7, wherein the shield has a diameter greater than the anode and is positionally aligned about centered on the wafer.

28. (Canceled).

29. (Currently amended) The method of claim 12, wherein the wafer is rotated ~~relative to the shield~~ during the electroplating process.